Zener Voltage Regulators

225 mW SOT-23 Surface Mount

This series of Zener diodes is offered in the convenient, surface mount plastic SOT-23 package. These devices are designed to provide voltage regulation with minimum space requirement. They are well suited for applications such as cellular phones, hand held portables, and high density PC boards.

Specification Features

- 225 mW Rating on FR-4 or FR-5 Board
- Zener Breakdown Voltage Range 2.4 V to 75 V
- Package Designed for Optimal Automated Board Assembly
- Small Package Size for High Density Applications
- ESD Rating of Class 3 (>16 kV) per Human Body Model
- Peak Power 225 W (8 X 20 μs)
- Pb-Free Package is Available

Mechanical Characteristics

CASE: Void-free, transfer-molded, thermosetting plastic case

FINISH: Corrosion resistant finish, easily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:

260°C for 10 Seconds

POLARITY: Cathode indicated by polarity band

FLAMMABILITY RATING: UL 94 V-0

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Peak Power Dissipation @ 20 μs (Note 1) @ $T_L \le 25$ °C	P _{pk}	225	Watts
Total Power Dissipation on FR–5 Board, (Note 2) @ T _A = 25°C Derated above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	556	°C/W
Total Power Dissipation on Alumina Substrate, (Note 3) @ T _A = 25°C Derated above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA}	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Nonrepetitive current pulse per Figure 9.

 $FR_{-5} = 1.0 \times 0.75 \times 0.62 \text{ in.}$ Alumina = 0.4 X 0.3 X 0.024 in, 99.5% alumina.

dzsc.com



ON Semiconductor

http://onsemi.com





CASE 318 STYLE 8

MARKING DIAGRAM



xxx = Specific Device Code = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
BZX84CxxxET1	SOT-23	3000/Tape & Reel
BZX84CxxxET1G	SOT-23 (Pb-Free)	3000/Tape & Reel
BZX84CxxxET3	SOT-23	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

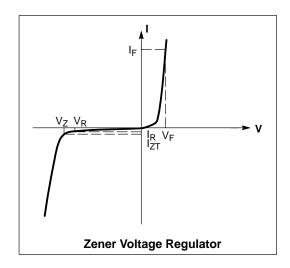
DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the Electrical Characteristics table on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS

(Pinout: 1-Anode, 2-No Connection, 3-Cathode) ($T_A = 25^{\circ}C$ unless otherwise noted, $V_F = 0.95$ V Max. @ $I_F = 10$ mA)

Symbol	Parameter				
V _Z	Reverse Zener Voltage @ I _{ZT}				
I _{ZT}	Reverse Current				
Z _{ZT}	Maximum Zener Impedance @ I _{ZT}				
I _R	Reverse Leakage Current @ V _R				
V _R	Reverse Voltage				
lF	Forward Current				
V _F	Forward Voltage @ I _F				
ΘV_Z	Maximum Temperature Coefficient of V _Z				
С	Max. Capacitance @ V _R = 0 and f = 1 MHz				



ELECTRICAL CHARACTERISTICS

(Pinout: 1-Anode, 2-No Connection, 3-Cathode) ($T_A = 25^{\circ}C$ unless otherwise noted, $V_F = 0.90 \text{ V}$ Max. @ $I_F = 10 \text{ mA}$) (Devices listed in *bold, italic* are ON Semiconductor Preferred devices.)

	Device	@ I	V _{Z1} (V) _{ZT1} = 5 (Note 4)	mΑ	Z _{ZT1} (Ω) @ I _{ZT1}	V _{Z2} @ I _{ZT2} (Not	= 1 mA	Z _{ZT2} (Ω) @ ! ZT2	V _{Z3} @ I _{ZT3} = (Not		Z _{ZT3} (Ω) @	Ma Revo Leak Curi	erse kage	θ _\ (m\ @ l _{ZT1}	,	C (pF) @ V _R = 0
Device	Mark- ing	Min	Nom	Max	= 5 mA	Min	Max	= 1 mA	Min	Max	I _{ZT3} = 20 mA	I _R @	V _R (V)	Min	Max	f = 1 MHz
BZX84C3V3ET1	BA4	3.1	3.3	3.5	95	2.3	2.9	600	3.6	4.2	40	5	1	-3.5	0	450
BZX84C4V7ET1	BA9	4.4	4.7	5	80	3.7	4.7	500	4.5	5.4	15	3	2	-3.5	0.2	260
BZX84C5V1ET1	BB1	4.8	5.1	5.4	60	4.2	5.3	480	5	5.9	15	2	2	-2.7	1.2	225
BZX84C5V6ET1	BB2	5.2	5.6	6	40	4.8	6	400	5.2	6.3	10	1	2	-2.0	2.5	200
BZX84C6V2ET1, G*	BB3	5.8	6.2	6.6	10	5.6	6.6	150	5.8	6.8	6	3	4	0.4	3.7	185
BZX84C6V8ET1	BB4	6.4	6.8	7.2	15	6.3	7.2	80	6.4	7.4	6	2	4	1.2	4.5	155
BZX84C7V5ET1	BB5	7	7.5	7.9	15	6.9	7.9	80	7	8	6	1	5	2.5	5.3	140
BZX84C10ET1	BB8	9.4	10	10.6	20	9.3	10.6	150	9.4	10.7	10	0.2	7	4.5	8.0	130
BZX84C12ET1	BC1	11.4	12	12.7	25	11.2	12.7	150	11.4	12.9	10	0.1	8	6.0	10.0	130
BZX84C15ET1	BC3	14.3	15	15.8	30	13.7	15.5	200	13.9	15.7	20	0.05	10.5	9.2	13.0	110
BZX84C16ET1	BC4	15.3	16	17.1	40	15.2	17	200	15.4	17.2	20	0.05	11.2	10.4	14.0	105
BZX84C18ET1	BC5	16.8	18	19.1	45	16.7	19	225	16.9	19.2	20	0.05	12.6	12.4	16.0	100
BZX84C24ET1	BC8	22.8	24	25.6	70	22.7	25.5	250	22.9	25.7	25	0.05	16.8	18.4	22.0	80
	Device		_{Z1} Belo _{ZT1} = 2		Z _{ZT1} Below @ I _{ZT1}	V _{Z2} E @ I _Z 0.1	T2 =	Z _{ZT2} Below @ I _{ZT4}		Selow = 10 m	Z _{ZT3} Below @ I _{ZT3}	Ma Revo Leak Curr	erse kage		k) Be-	C (pF) @ V _R = 0
Device	Mark- ing	Min	Nom	Max	= 2 mA	Min	Max	= 0.5 mA	Min	Max	= 10 mA	I _R @ μΑ	V _R (V)	Min	Max	f = 1 MHz
BZX84C27ET1	BC9	25.1	27	28.9	80	25	28.9	300	25.2	29.3	45	0.05	18.9	21.4	25.3	70
BZX84C43ET1	BK6	40	43	46	150	39.7	46	375	40.1	46.5	80	0.05	30.1	37.6	46.6	40

^{*} The "G" suffix indicates Pb–Free package available.
4. Zener voltage is measured with a pulse test current I_Z at an ambient temperature of 25°C

TYPICAL CHARACTERISTICS

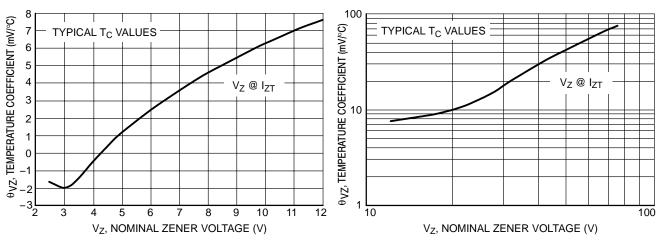


Figure 1. Temperature Coefficients (Temperature Range –55°C to +150°C)

Figure 2. Temperature Coefficients (Temperature Range –55°C to +150°C)

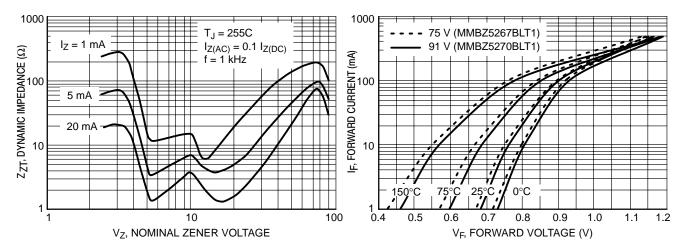


Figure 3. Effect of Zener Voltage on Zener Impedance

Figure 4. Typical Forward Voltage

TYPICAL CHARACTERISTICS

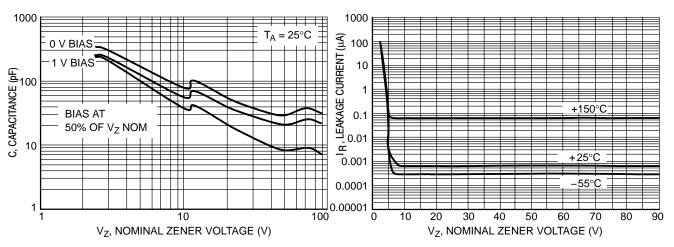


Figure 5. Typical Capacitance

Figure 6. Typical Leakage Current

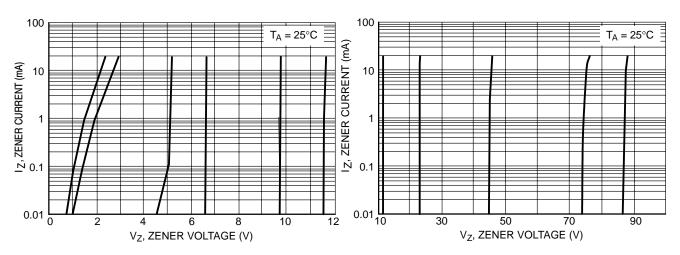


Figure 7. Zener Voltage versus Zener Current (V_Z Up to 12 V)

Figure 8. Zener Voltage versus Zener Current (12 V to 91 V)

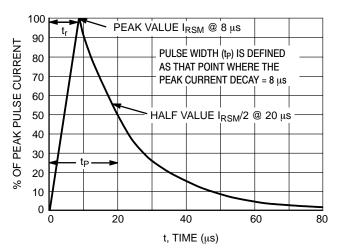
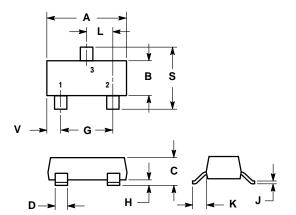


Figure 9. $8 \times 20 \mu s$ Pulse Waveform

PACKAGE DIMENSIONS

SOT-23 TO-236AB CASE 318-09 **ISSUE AJ**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. MAXIUMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL
- MATERIAL.

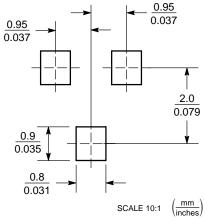
 4. 318-01, -02, AND -06 OBSOLETE, NEW STANDARD 318-09.

	INC	CHES	MILLIMETERS				
DIM	MIN	MAX	MIN	MAX			
Α	0.1102	0.1197	2.80	3.04			
В	0.0472	0.0551	1.20	1.40			
С	0.0385	0.0498	0.99	1.26			
D	0.0140	0.0200	0.36	0.50			
G	0.0670	0.0826	1.70	2.10			
Н	0.0040	0.0098	0.10	0.25			
J	0.0034	0.0070	0.085	0.177			
K	0.0180	0.0236	0.45	0.60			
L	0.0350	0.0401	0.89	1.02			
S	0.0830	0.0984	2.10	2.50			
V	0.0177	0.0236	0.45	0.60			

STYLE 8:

PIN 1. ANODE 2. NO CONNECTION 3. CATHODE

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082–1312 USA Phone: 480–829–7710 or 800–344–3860 Toll Free USA/Canada Fax: 480–829–7709 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2–9–1 Kamimeguro, Meguro–ku, Tokyo, Japan 153–0051 Phone: 81–3–5773–3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.